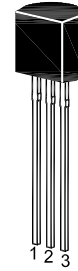


NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into six groups, D, E, F, G, H and I, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Base 3. Collector
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	30	V
Collector Emitter Voltage	V_{CEO}	20	V
Emitter Base Voltage	V_{EBO}	4	V
Collector Current	I_C	25	mA
Power Dissipation	P_{tot}	400	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 5\text{ V}$, $I_C = 1\text{ mA}$ Current Gain Group	D				
	E				
	F				
	G				
	H				
	I				
Collector Base Cutoff Current at $V_{CB} = 30\text{ V}$	I_{CBO}	-	-	100	nA
Emitter Base Cutoff Current at $V_{EB} = 3\text{ V}$	I_{EBO}	-	-	100	nA
Collector Base Breakdown Voltage at $I_C = 100\text{ }\mu\text{A}$	$V_{(BR)CBO}$	30	-	-	V
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CEO}$	20	-	-	V
Emitter Base Breakdown Voltage at $I_E = 100\text{ }\mu\text{A}$	$V_{(BR)EBO}$	4	-	-	V
Collector Emitter Saturation Voltage at $I_C = 10\text{ mA}$, $I_B = 1\text{ mA}$	$V_{CE(sat)}$	-	0.1	0.3	V
Base Emitter on Voltage at $V_{CE} = 5\text{ V}$, $I_C = 1\text{ mA}$	$V_{BE(on)}$	-	0.72	-	V
Collector Base Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{cbo}	-	1.2	1.6	pF
Gain Bandwidth Product at $V_{CE} = 5\text{ V}$, $I_C = 1\text{ mA}$	f_T	400	620	-	MHz

